Gigahertz Quantized Charge Pumping in Bottom-Gate-Defined InAs Nanowire Quantum Dots

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Supporting Information

ABSTRACT: Semiconducting nanowires (NWs) are a versatile, highly tunable material platform at the heart of many new developments in nanoscale and quantum physics. Here, we demonstrate charge pumping, that is, the controlled transport of individual electrons through an InAs NW quantum dot (QD) device at frequencies up to 1.3 GHz. The QD is induced electrostatically in the NW by a series of local bottom gates in a state of the art device geometry. A periodic modulation of a single gate is enough to obtain a dc current proportional to the frequency of the modulation. The dc bias, the modulation amplitude and the gate voltages on the local gates can be used to control the number of charges conveyed per cycle. Charge pumping in InAs NWs is relevant not only in metrology as a current standard, but also opens up the opportunity to investigate a variety of exotic states of matter, for example, Majorana modes, by single electron spectroscopy and correlation experiments.

KEYWORDS: charge pumping, nanowires, radio frequency, nonequilibrium dynamics, bottom gates

Epitaxially grown semiconducting nanowires (NWs) are versatile material platforms with myriads of fundamental and practical applications. InSb and InAs NWs are at the heart of several conceptually new experiments, for example, in the search for Majorana bound states, or in a Cooper pair splitter, a potential source of entangled electron pairs. Many NWs are optically active and can be incorporated in highly tunable device geometries. The spin coherence times and large g-factors are ideal to form and manipulate quantum bits. New measurement paradigms like initialization and coherent control of quantum bits, dynamic quantum control, or single electron spectroscopy and correlation measurements require the fast manipulation of individual electrons on the scale of several hundred MHz. The controlled transport of single electrons can be achieved in a process called “quantized charge pumping” (CP), in which a periodic modulation of one or several external parameters leads to a dc current of one electron per cycle. For many years, the driving force for the development of CP was the creation of a new current standard in metrology. Recent theoretical proposals suggest that CP can be used well beyond a current standard, for example, to investigate and characterize exotic electron states like fractional quantum Hall states. Specifically, CP in NW devices was proposed to identify Majorana bound states, or fractional Fermions. Very recent experiments in two-dimensional electron gases (2DEGs) have already demonstrated an on-demand source for electron pairs with potentially nonclassical correlations.

CP driven by electrical gates at frequencies of up to a few megahertz was demonstrated in channels of a 2DEG, in metallic single electron transistors, in InAs NWs, and in carbon nanotubes. Higher gating frequencies became accessible recently in 2DEGs, Si-based field-effect transistors, and graphene. An essential step for applications and more involved experiments was the demonstration of CP by modulating only a single external parameter.

Here, we present single-parameter quantized CP in InAs NW QDs defined and controlled by local bottom gates and a global backgate with a device geometry and material choices similar to the most recent advanced low-frequency NW experiments. We find current steps for frequencies up to 1.3 GHz, which corresponds to a dc current of 208.4 pA. We investigate the dependence of CP on the gate voltages, bias and applied rf power and discuss nonequilibrium effects at high frequencies. Our results demonstrate the feasibility of using CP as a tool to investigate novel phenomena in semiconducting NWs, such as Majorana bound states or Cooper pair splitting. In addition,
NWs are promising for studying nonequilibrium quantum phenomena and for improved current standards because the low effective electron mass results in a large energy level spacing.

The mechanism of single-parameter nonadiabatic CP is shown schematically in Figure 1a. Local electrical gates define two tunnel barriers (left and right, L and R, respectively), forming a QD with discrete electron states separated by the Coulomb charging and level spacing energies. A central gate (M) can be used to fine-tune the QD energies. A periodic voltage modulation on gate L leads to a modulation of the left potential barrier. In the loading phase (i) of a CP cycle, the left barrier is low and an empty QD state is filled by an electron when below the Fermi energy, $E_F$, of the leads (depicted for zero bias). In the subsequent decoupling phase (ii), the left barrier is increased, which prohibits the electron from tunneling back into lead L and lifts the filled state above $E_F$ due to the capacitive coupling to the QD. In the unloading phase (iii) the QD state reaches above the right barrier and the electron leaves into the empty states of the right contact. In the second half of the modulation, the left barrier and the now empty QD state are lowered again while the right barrier prohibits the QD from being charged from the right. At any time of the cycle, the static dc conductance through the structure is negligible. At most times, the electrons in the QD are not in thermal equilibrium with the contacts (“nonadiabatic”), and at frequencies higher than the energy relaxation rate, the QD level occupation also can be nonthermal (“hot electrons”). If each cycle transfers on average one electron per state from the left to the right, the resulting average dc current is

$$I_{dc} = nef$$

with $n$ the number of electron states accessible for CP, $e$ the elementary charge and $f$ the frequency of the modulation. As demonstrated below, $n$ can be controlled by various parameters, such as gate voltages, dc bias and modulation amplitudes, which leads to steps between well-defined current levels as a function of the respective parameter.

A scanning electron microscopy (SEM) image of a NW charge pump is shown in Figure 1b. It consists of an array with 12 local gates fabricated by electron beam lithography on a highly doped silicon substrate that serves as a global backgate, insulated by ~400 nm SiO$_2$. The ~50 nm wide local gates consist of 4 nm of Ti and 18 nm of Pt with an edge-to-edge separation of ~60 nm. These gates are overgrown by ~25 nm SiN$_x$ for electrical insulation using plasma-enhanced chemical vapor deposition. The SiN$_x$ was removed at the ends of the gates by a reactive ion etch with CHF$_3$/O$_2$ for electrical contact. In the next steps, we deposit a single InAs NW (~70 nm diameter) perpendicular to the gate axes using micro-manipulators. The NWs were grown by solid-source molecular beam epitaxy, implementing a two-step growth process to suppress stacking faults. Two Ti/Pd (5/100 nm) contacts were fabricated after an Ar plasma etch to remove the native oxide at the ends of the NW.

Figure 1b also shows the measurement setup. A QD is formed using the central three bottom gates, labeled left (L), middle (M), and right (R) with the corresponding gate voltages $V_L$, $V_M$, and $V_R$. The remaining gates are held constant at 1 V. A standard frequency generator supplies a sinusoidal radio frequency (rf) superimposed to the dc voltage on gate L using a commercial bias-tee at room temperature. This signal is fed into an rf line connected to the left gate. All other lines are standard twisted pair copper cables. The sample is mounted on a printed circuit board and resides in a vacuum chamber immersed in a bath of liquid helium at 4.2 K. A dc bias is applied on the right NW contact, whereas a standard room-temperature current—voltage (IV) converter is used to read out the dc current through the left NW end to ground.

The dc current through the device, $I_{dc}$, without an rf excitation is plotted in Figure 1c as a function of the barrier gate voltages $V_L$ and $V_R$, with a bias of $V_M = 1$ mV and the middle gate set to $V_M = -200$ mV. Coulomb blockade resonances can be discriminated down to $V_L \approx -3$ V and $V_R \approx -2$ V, where the transport characteristics are dominated by a single QD (see Supporting Information, Figure S1). At higher voltages, the system exhibits a larger conductance and a more complex pattern. From standard transport spectroscopy in the single dot regime, we obtain an addition energy of $E_{add} \approx 7$ meV, with a level spacing of ~1 meV. All CP experiments presented below were obtained at strongly negative barrier gate voltages, where the dc current without CP, shown in Figure 1d, is too small to be detected in our setup, that is, $I_{dc} < 10$ fA. The IV converter has a current offset of 2–4 pA that is not subtracted from the data.

Figure 2a shows the dc current through the NW as a function of the left and right barrier gate voltages with a sinusoidal modulation at $f = 5$ MHz and the power $P = 2$ dBm on $V_L$. In all experiments the dc bias is set to $V_{sd} = 1$ mV. The resulting current shows plateaus of constant current bounded by sharp transitions to the next higher values. This step structure can be seen clearly in Figure 2b, where a cross section of the data at constant $V_R$ (dashed vertical line in Figure 2a) is plotted as a function of $V_L$. Five quantized current plateaus occur at $I = nef$, indicated by horizontal dashed lines. The step size is $\Delta I = 0.80$
higher states and subsequent energy relaxation can still lead to the loading phase. However, electrons tunneling into energetically lower states at the minimum of the confinement phase (AB) of the rf cycle, \( \Delta E_{add}/\Delta E_{add} \approx 1.9 \), see Supporting Information eq S8. This result is quite intuitive because of the deeper and stronger confinement expected in the unloading phase, but contradicts many theoretical assumptions and estimates used in the literature.

CP is limited at the vertical lines CD when the right barrier is too low and the QD is not emptied reliably to the right because of back-tunneling from the right contact. In contrast to other experiments, in our measurements, the CP current tends to zero and does not increase, as one might expect when both barriers are low.

We now turn to the question of how the pattern in Figure 2 evolves with increasing frequency. Figure 3a shows the CP current as a function of \( V_L \) and \( V_R \) at \( f = 40 \) MHz, with a cross section at \( V_R = -2.46 \) V plotted in Figure 3b. The applied rf power is \( P = 2 \) dBm. Also here, the current steps due to CP are well defined and exhibit a similar gate dependence as at 5 MHz. The current step size is \( \Delta I = 6.4 \) pA, in agreement with ideal CP, with a relative accuracy of the current steps similar to lower frequencies. The main difference to 5 MHz is that the vertical transitions AB appear broadened and seem to consist of several parallel features (see inset). The current steps in cross sections parallel to the lines AD (not shown) appear washed out, whereas the vertical cross sections still exhibit clearly defined plateaus.

At \( f = 800 \) MHz, the dc current shown in Figure 3c exhibits plateaus with \( \Delta I = 128.2 \) pA steps and well-defined transitions along the AB lines, but strongly washed out along AD. The applied rf power is \( P = 10 \) dBm, but damping due to stray capacitances leads to a reduced rf power on the left gate and a reduced number of visible plateaus compared to the experiments at lower frequencies. In the cross section in Figure 3d, one finds that not all plateaus at \( I = ef \) are flat, but can exhibit a
which electrons in excited states can tunnel back into the left contact more easily due to the lower barrier when crossing the Fermi energy. This leads to the observed smearing of the lines along AB and also accounts qualitatively for the sloped plateaus. We expect that this smearing would be considerably stronger for materials with a larger effective mass. Another nonequilibrium effect is the increasing separation of the BC lines with increasing frequency. If the time window of the loading process becomes shorter than the electron energy relaxation time, the states can only be charged by direct tunneling when aligned with $E_F$ at more positive $V_{L}$ in contrast to low frequency CP, where energy relaxation allows the loading of the ground state at lower $V_{L}$ via excited states. This results in a spacing of the BC lines determined by the addition energy, similar to the AD lines, in rough agreement with the experiments at higher frequencies.

We now investigate the CP current as a function of other external parameters. The frequency dependence of the dc current plateaus is plotted in Figure 4a. The symbols are the experimental values, whereas the straight lines are given by $I_{dc} = n e f$ without adjustable parameters. The inset shows the denser low-frequency points. (b) $I_{dc}$ as a function of the applied rf power $P_{rf}$ and the left gate voltage, $V_{L}$. (c) $I_{dc}$ as a function of the bias, $V_{sd}$, and $V_{L}$. The colorscale is limited to positive values. For $V_{sd} < -23$ mV the current is negative and increases continuously in amplitude. The insets of the colorscale images are the absolute values of the gradient of $I_{dc}$. (d) Cross section of (c) at $V_{sd} = 10$ mV.

The frequency dependence of the CP current on the rf power $P$ is investigated in Figure 4b for $V_{L}$-sweeps at $f = 50$ MHz and constant $V_{sd} = -2.45$ V. We cannot detect CP for powers below $-8$ dBm. With increasing CP power $P$ is limited to an increasing interval in $V_{L}$. The more positive $V_{L}$ limit is determined by the
unloading process (line AD in Figure 2d), and the more negative by the loading-limited BC line. The evolution of these lines with power is very well described by eqs S3 and S5 of our simple model in the Supporting Information, using the conversion of power to the applied voltage \( V_{sd} [mV] = 0.22 \times 10^{p(dBm)/20} \) and a frequency-dependent prefactor. The latter is about 1 at the lower frequencies shown here and decreases for higher frequencies. These experiments can in principle be used directly to calibrate the power applied to the gates.

In Figure 4c, we plot the CP current as a function of \( V_L \) and the bias, \( V_{sd} \) applied to the right contact, for \( f = 40 \text{ MHz} \). A cross section at \( V_{sd} = 10 \text{ mV} \) is shown in Figure 3d. The colorscale is limited to positive values because for \( V_{sd} < -23 \text{ mV} \), the current evolves continuously, that is, without steps, to very strongly negative values. For \( V_{sd} > -23 \text{ mV} \), we find a positive current and very sharp and well-defined current plateaus, demonstrating that electrons can also be pumped against a significant bias in our NW pumps. The breakdown of CP and the strong negative current for a strongly negative bias is due to the bias distorting the left tunnel barrier and the left Fermi energy reaching above the left potential barrier at least at the maximum voltage of the rf cycle. Because the current steps cease roughly at the same bias, the effect by the capacitive coupling from the left contact to the QD can be neglected. However, this source capacitance is responsible for the stepwise change in \( I_{lp} \) with the bias at more positive \( V_L \).

In summary, we report the fabrication and detailed characterization of an InAs NW based single-parameter charge pumping device up to GHz frequencies. We discuss in detail the dependencies on rf power, bias, and gate voltages, which is possible due to the multipile-gate design of the device. On the one hand, this proof of concept opens up the important possibilities of using CP as a novel spectroscopy tool to investigate correlated electron systems and exotic transport processes in NWs, for example, in a Cooper pair splitter or Majorana zero modes, where CP might reduce background fluctuations like shot noise to improve the visibility of cross correlation signals.

**ASSOCIATED CONTENT**

Supporting Information

- Quantum dot characteristics in the single-dot regime.
- Electrostatic model of quantized charge pumping.

The Supporting Information is available free of charge on the ACS Publications website at DOI: 10.1021/acs.nanolett.5b01190.

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**REFERENCES**


